ODIS, Inc.
3 Corporate Drive
Suite 204
Shelton, CT 06484
401-338-1212

Research & Development Facility
University of Connecticut
Merritt Building
54 Ahern Lane
Storrs, CT. 06269-5235

NEWS RELEASE

ODIS Receives Air Force Research Laboratory (AFRL) Contract

"A Breakthrough Technology for Air, Space and Security Applications"

Shelton, Ct. January 19, 2010 – ODIS, Inc., announced today that it recently received a $750,000 Award to develop "Monolithic Infra-Red Pixel Structures Enabled by Thyristor-HFET EO Logic". Infra-Red technologies currently require cryogenic cooling to operate and use independent readout integrated circuits. The ODIS technology has been developed to provide the new "state of the art" in integrated approaches to infrared imaging combined with transistor readout circuits.

Dr. Geoff Taylor, Chief Scientist, ODIS, Inc., states that by incorporating these technologies on the same epitaxial structure, the electro-optic operation should enable high sensitivity infra-red imaging in an uncooled environment with significantly improved operating speeds and off-chip communications.

"This breakthrough technology not only has the potential to produce tremendous cost savings for the U.S. Air Force and Space Missile Command," said Leon (Lee) Pierhal, President, ODIS, Inc. "We expect enhanced reliability and higher resolution for current and future satellite missions. In addition, the technology should be able to reduce the cost and improve performance for several commercial markets which become viable with this new capability".

At the heart of this technology is ODIS's new and patented semiconductor fabrication process, POET, (Planer OptoElectric Technology) which is based on a novel Group III-V materials structure. POET is a patented Group III-V materials system that supports monolithic fabrication of ICs containing active and passive optical elements, together with high-performance analog and digital elements, allowing the economical integration of many optical devices together with dense, high-speed analog and high-speed, low-power digital elements in monolithic ICs.

About ODIS Incorporated

ODIS, Inc., (Opel Defense Integrated Systems), a Delaware Corporation, headquartered in Shelton, CT. with offices in Rhode Island and Research and Development facilities located on the campus of the University of Connecticut. ODIS designs communications transceivers, optoelectric integrated platforms and infrared sensor type products for military and industrial applications.

A leader in gallium arsenide III-V compound structures the Company has been awarded 39 patents and has eight more patents pending. For more information about ODIS Inc., please visit the ODIS Tab at www.opelinc.com.

ON BEHALF OF THE BOARD OF DIRECTORS

Michael McCoy, Secretary

For further information:

Leon M. Pierhal
President
Tel: (401) 338-1212
Email: leepierhal@aol.com

Bill Blase, Cathy Loos, or Stephanie Kuffner
Media Relations – WT Blase & Associates Inc.
Tel: (212) 221-1079